

2SA18900RL Datasheet



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DiGi Electronics Part Number 2SA18900RL-DG

Manufacturer Panasonic Electronic Components

Manufacturer Product Number 2SA18900RL

Description TRANS PNP 80V 1A MINIP3-F1

Detailed Description Bipolar (BJT) Transistor PNP 80 V 1 A 120MHz 1 W S

urface Mount MiniP3-F1



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
2SA18900RL	Panasonic Electronic Components
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	1 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
80 V	300mV @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	120 @ 100mA, 2V
Power - Max:	Frequency - Transition:
1 W	120MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-243AA	MiniP3-F1
Base Product Number:	
2SA1890	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	ECCN:
1 (Unlimited)	EAR99
HTSUS:	
8541.29.0075	

2SA1890

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SC5026

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- ullet High collector-emitter voltage (Base open) V_{CEO}
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-80	V	
Collector-emitter voltage (Base open)	V_{CEO}	-80	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_{C}	-1	A	
Peak collector current	I_{CP}	-1.5	A	
Collector power dissipation *	P _C	1	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	o°C (

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 1.5±0.1 1 : Base 2 : Collector 3 : Emitter MiniP3-F1 Package

■ Electrical Characteristics $T_a = 25$ °C ± 3°C

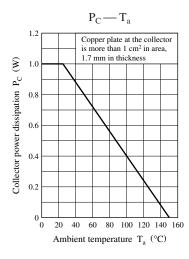
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-80			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-80			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -40 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Forward current transfer ratio	h _{FE1} *2	$V_{CE} = -2 \text{ V}, I_{C} = -100 \text{ mA}$	120		340	_
	h _{FE2} *1	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	60			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.3	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		15	30	pF
(Common base, input open circuited)						

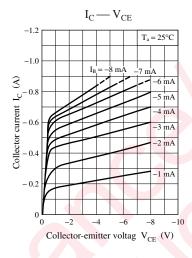
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

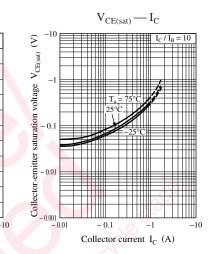
2. *1: Pulse measurement

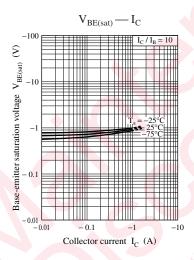
*2: Rank classification

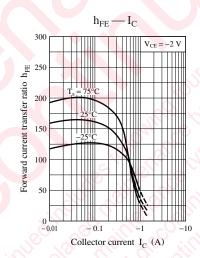
Rank	R	S
h _{FE1}	120 to 240	170 to 340

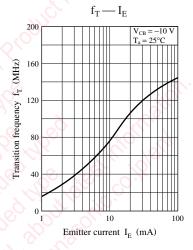


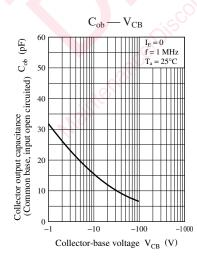












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